Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method of forming a three-dimensional device, the device including at least a first thin film device layer having a plurality of first electrodes and a second thin film device layer having a plurality of second electrodes, each deposited in a thickness direction, the method comprising:

forming the first thin film device layer on a first substrate;

forming the second thin film device layer on a second substrate with a separable layer therebetween;

adhering the first thin film device layer to the second thin film device layer such that the plurality of first electrodes are electrically connected to the plurality of second electrodes; and

irradiating the separable layer with light to cause a separation, such that the second thin film device layer is transferred from the second substrate to the first substrate, and formed on the first thin film device layer.

2. (Currently Amended) A method of forming a three-dimensional device, the device including at least a first thin film device layer having a plurality of first electrodes and a second thin film device layer having a plurality of second electrodes constituting a three-dimensional circuit, each thin film device layer deposited in a thickness direction,; each thin film device layer constituting a circuit disposed in a predetermined region extending in a planar direction, the method comprising:

adhering the first thin film device layer to the second thin film device layer such that the plurality of first electrodes are electrically connected to the plurality of second electrodes; and

depositing the second thin film device layer on the first thin film device layer by a separation in a separable layer on which the second thin film device layer is formed.

3. (Previously Amended) The method of forming a three-dimensional device according to claim 1, further comprising irradiating the separable layer with light to cause a separation in at least one of the separable layer and at an interface between the separable layer and the second substrate so that the second thin film device layer on the second substrate is transferred to the first substrate of the three-dimensional device.

4. (Previously Amended) The method of forming a three-dimensional device according to claim 3, the separation of the separable layer being caused by one of breakage and weakening of interatomic or intermolecular bonds in a material constituting the separable layer.

5. (Previously Amended) The method of forming a three-dimensional device according to claim 3, the separation of the separable layer being caused by evolution of gas from a material constituting the separable layer.

6. (Previously Amended) The method of forming a three-dimensional device according to claim 3, the light being a laser beam.

7. (Previously Amended) The method of forming a three-dimensional device according to claim 3, the separable layer comprising one of amorphous silicon, ceramic, metal, and organic polymeric material.

8. (Previously Amended) The method of forming a three-dimensional device according to claim 1, each thin film device layer comprising electrodes electrically connecting two adjacent thin film device layers to each other.

9. (Previously Amended) The method of forming a three-dimensional device according to claim 8, the connecting electrodes being provided on both surfaces of each thin film device layer.

10. (Previously Amended) The method of forming a three-dimensional device according to claim 8, the three dimensional device further comprising an anisotropic conductive film, the method further comprising joining two adjacent thin film device layers to each other with the anisotropic conductive film therebetween.

11. (Previously Amended) The method of forming a three-dimensional device according to claim 1, in two selected layers of the thin film device layers, a first layer has a light-emitting section and a second layer has a light-receiving section, the light-emitting section and the light-receiving section enabling optical communication between the two layers.

12. (Previously Amended) The method of forming a three-dimensional device according to claim 1, the second thin film device layer deposited by transferring being formed simultaneously with at least one other of the thin film device layers.

13. (Previously Amended) The method of forming a three-dimensional device according to claim 1, at least one of the thin film device layers comprising a plurality of thin film transistors.

14. (Previously Amended) The method of forming a three-dimensional device according to claim 1, at least one of the thin film device layers comprising a memory cell array.

15. (Previously Amended) The method of forming a three-dimensional device according to claim 1, a plurality of layers among the thin film device layers comprising one memory.

16. (Previously Amended) The method of forming a three-dimensional device according to claim 1, at least one of the thin film device layers comprising a memory cell array, and at least one other thin film device layers comprises a logic circuit.

17. (Previously Amended) The method of forming a three-dimensional device according to claim 16, the logic circuit being capable of driving the memory cell array.

18. (Previously Amended) The method of forming a three-dimensional device according to claim 16, the logic circuit and the memory cell array being formed in accordance with different design rules.

19. (Previously Amended) The method of forming a three-dimensional device according to claim 16, the logic circuit and the memory cell array being formed in accordance with different design parameters.

20. (Previously Amended) The method of forming a three-dimensional device according to claim 16, the logic circuit and the memory cell array being formed by different fabricating processes.

21. (Currently Amended) A method for manufacturing a three-dimensional device having a plurality of thin film device layers on a first substrate, the plurality of thin film device layers including at least a first thin film device layer having a plurality of first electrodes and a second thin film device layer having a plurality of second electrodes, the method comprising:

forming the second thin film device layer on a second substrate with a separable layer therebetween; ~~and~~

adhering the first thin film device layer to the second thin film device layer such that the plurality of first electrodes are electrically connected to the plurality of second electrodes; and

irradiating the separable layer with light to cause a separation in at least one of the separable layer and at an interface so that the second thin film device layer is transferred to the first substrate.

22. (Previously Amended) The method for manufacturing a three-dimensional device according to claim 21, the separation of the separable layer being caused by one of breakage and weakening of interatomic or intermolecular bonds in a material constituting the separable layer.

23. (Previously Amended) The method for manufacturing a three-dimensional device according to claim 21, the separation of the separable layer being caused by evolution of gas from a material constituting the separable layer.

24. (Previously Amended) The method for manufacturing a three-dimensional device according to claim 21, the light being a laser beam.

25. (Previously Amended) The method for manufacturing a three-dimensional device according to claim 21, the second thin film device layer being deposited by transferring being formed simultaneously with at least one other of the thin film device layers.

26. (Previously Added) The method for manufacturing a three-dimensional device according to claim 21, at least one of the plurality of thin film device layers having a light-emitting section.

27. (Previously Added) The method for manufacturing a three-dimensional device according to claim 21, further comprising a step of forming a light-emitting section in at least one of the plurality of thin film device layers.